

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

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1.-63. Canceled.

64. (Currently Amended) A nitride semiconductor light-emitting device comprising:

an n-type layer comprising an n-type GaN or ~~and~~ n-type nitride semiconductor containing indium and gallium;

a first p-type clad layer comprising a p-type InGaN containing indium and gallium;

an active layer, provided between said n-type and first p-type ~~nitride semiconductor~~ clad layers, having a multi-quantum well structure having a well layer comprising a nitride semiconductor represented by ~~$\text{In}_x\text{Ga}_{1-y}\text{N}$, $0 \leq y < 1$~~ $\text{In}_x\text{Ga}_{1-x}\text{N}$, $0 < x \leq 1$;

a second p-type clad layer made of a p-type AlGaN containing Al and Ga provided over said first p-type clad layer; and

a p-type contact layer formed of a p-type GaN provided over said second p-type clad layer.

65. Canceled.

66. (Previously Presented) The device according to claim 71, further comprising a p-type contact layer formed of a p-type GaN provided over said second p-type clad layer, and an n-type contact layer formed of an n-type GaN and over which said second n-type clad layer is provided.

67.-70. Canceled.

71. (Previously Presented) A nitride semiconductor light-emitting device comprising:

a first n-type clad layer comprising an n-type nitride semiconductor containing indium and gallium;

a first p-type clad layer comprising a p-type InGaN containing indium and gallium;

an active layer provided between said first n-type and p-type clad layers and having a multi-quantum well structure including a well layer comprising a nitride semiconductor represented by $\text{In}_x\text{Ga}_{1-x}\text{N}$, where $0 < x < 1$, and a barrier layer comprising a nitride semiconductor represented by $\text{In}_y\text{Ga}_{1-y}\text{N}$, where $0 \leq y < 1$;

a second n-type clad layer comprising an n-type nitride semiconductor containing aluminum and gallium, said second n-type clad layer having a larger band gap than said first n-type clad layer, said second n-type clad layer being provided over said first n-type clad layer; and

a second p-type clad layer comprising a p-type AlGaIn containing aluminum and gallium, said second p-type clad layer having a larger band gap than said first p-type clad layer, and said second p-type clad layer being provided over said first p-type clad layer.